

RM3 - RM3C

SILICON RECTIFIER DIODES

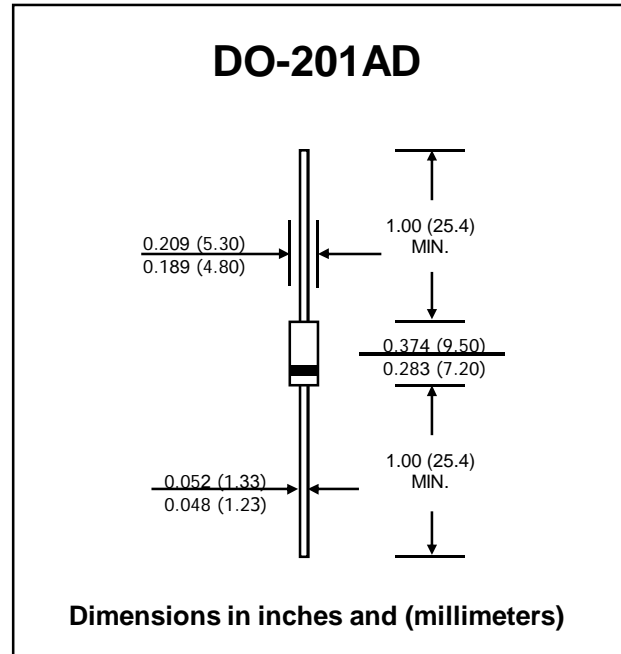
PRV : 400 - 1000 Volts
Io : 2.5 Ampere

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : DO-201AD Molded plastic
- * Epoxy : UL94V-0 rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 1.21 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

RATING	SYMBOL	RM3	RM3B	RM3C	UNIT
Maximum Reverse Voltage	V_{RM}	400	800	1000	V
Maximum Peak Reverse Surge Voltage	V_{RSM}	400	800	1000	V
Maximum Average Forward Current	$I_{F(AV)}$	2.5			A
Maximum Peak Forward Surge Current Half-cycle Sine wave, 50 Hz, Single Shot	I_{FSM}	150			A
Maximum Forward Voltage at $I_F = 2.5 A$	V_F	0.95			V
Maximum Reverse Current at $V_R = V_{Rmax}$	I_R	10			μA
	$I_{R(H)}$	100			μA
Junction Temperature Range	T_J	- 40 to + 150			°C
Storage Temperature Range	T_{STG}	- 40 to + 150			°C

RATING AND CHARACTERISTIC CURVES (RM3 - RM3C)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

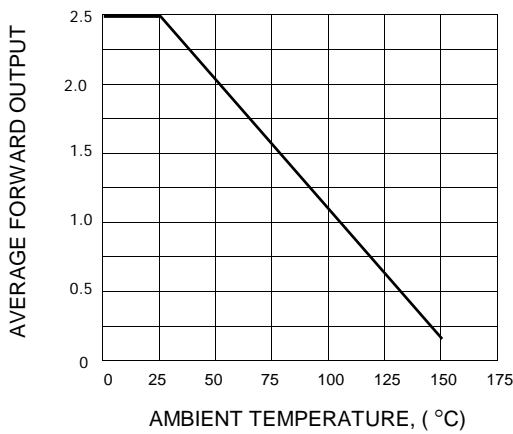


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

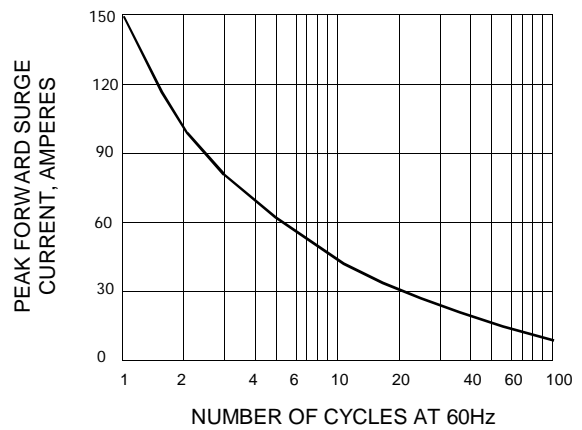


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

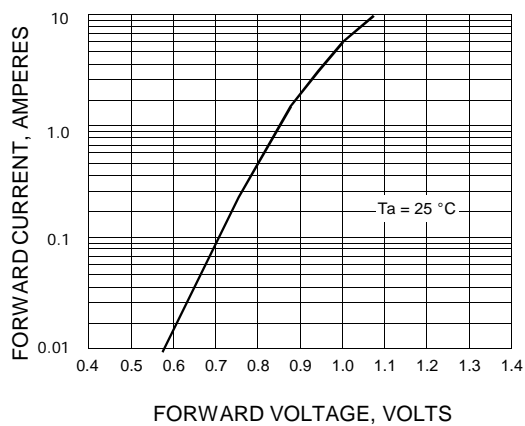


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

